

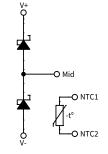
1200 V, 600 A, Silicon Carbide, Half-Bridge Rectifier

| $V_{_{\rm R}}$ | 1200 V |
|----------------|--------|
| I <sub>F</sub> | 600 A  |

#### **Technical Features**

- Ultra-Low Loss, High Frequency Operation
- Low Forward Voltage (V<sub>F</sub>) Drop with Positive Temperature Coefficient
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Temperature-Independent Switching Behavior





### **Applications**

- Railway, Traction, and Motor Drives
- EV Chargers
- High-Efficiency Converters / Inverters
- Renewable Energy
- Smart-Grid / Grid-Tied Distributed Generation

### **System Benefits**

- Enables Compact, Lightweight Systems
- Increased System Efficiency, due to Low Switching & Conduction Losses of SiC
- Reduced Thermal Requirements and System Cost

### **Maximum Parameters (Verified by Design)**

| Parameter                            | Symbol                  | Min. | Тур. | Max. | Unit | Test Conditions  | Note |
|--------------------------------------|-------------------------|------|------|------|------|--|------|
| Maximum Reverse Voltage              | V <sub>R-Max</sub>      |      |      | 1200 | V    |  |      |
| Continuous Famural Comment           |                         |      | 908  |      |      | T <sub>C</sub> = 25°C, T <sub>VJ</sub> ≤ 175°C           |      |
| Continuous Forward Current           | IF                      |      | 642  |      |      | T <sub>C</sub> = 90°C, T <sub>VJ</sub> ≤ 175°C           |      |
| Maximum Pulsed Forward Current       | I <sub>F (Pulsed)</sub> |      |      | 1200 | A    | $t_{Pmax}$ limited by $T_{VJmax}$<br>$T_C = 25^{\circ}C$ |      |
| Maximum Virtual Junction Temperature | T <sub>v</sub> ,        | -40  |      | 175  | °C   |  |      |

# Diode Characteristics (Per Position) ( $T_{VJ} = 25$ °C unless otherwise specified)

| Parameter                            | Symbol             | Min. | Тур.  | Max. | Unit | <b>Test Conditions</b>                           | Note |
|--------------------------------------|--------------------|------|-------|------|------|--|------|
| Diada Farruard Valtarra              | .,                 |      | 1.5   |      | V    | I <sub>F</sub> = 600 A                           |      |
| Diode Forward Voltage                | V <sub>F</sub>     |      | 2.0   |      |      | I <sub>F</sub> = 600 A, T <sub>VJ</sub> = 175°C  |      |
| Develope Comment                     |                    |      | 0.16  |      | А    | V <sub>R</sub> = 1200 V, T <sub>VJ</sub> = 25°C  |      |
| Reverse Current                      | I <sub>R</sub>     |      | 0.90  |      | mA   | V <sub>R</sub> = 1200 V, T <sub>VJ</sub> = 175°C |      |
| Total Capacitive Charge              | Qc                 |      | 3.5   |      | mC   | V <sub>R</sub> = 800 V                           |      |
|                                      |                    |      | 45.3  |      |      | V <sub>R</sub> = 0 V, f = 100 kHz                |      |
| Total Capacitance                    | С                  |      | 3.2   |      | nF   | V <sub>R</sub> = 400 V, f = 100 kHz              |      |
|                                      |                    |      | 2.5   |      |      | V <sub>R</sub> = 800 V, f = 100 kHz              |      |
| Thermal Resistance, Junction to Case | R <sub>TH-JC</sub> |      | 0.063 |      |      | Per position                                     |      |

#### Note:

 $<sup>^1</sup>$ SiC Schottky diodes are majority carrier devices, so there is no reverse recovery charge.

### **Module Physical Characteristics**

| Parameter                          | Symbol            | Min.  | Тур.  | Max. | Unit | Test Conditions                 |
|------------------------------------|-------------------|-------|-------|------|------|---------------------------------|
| Package Resistance, M1 (High-Side) | R <sub>1-2</sub>  |       | 106.5 |      | 0    | T <sub>c</sub> = 125°C, Note 1  |
| Package Resistance, M2 (Low-Side)  | R <sub>2-3</sub>  |       | 126.3 |      | μΩ   | T <sub>c</sub> = 125°C, Note 1  |
| Stray Inductance                   | $L_{Stray}$       |       | 4.9   |      | nH   | Between DC- and DC+, f = 10 MHz |
| Case Temperature                   | T <sub>c</sub>    | -40   |       | 125  | °C   |                                 |
| Manustina Tanana                   |                   | 3     | 4.5   | 5    | N-m  | Baseplate, M6 bolts             |
| Mounting Torque                    | Ms                | 0.9   | 1.1   | 1.3  |      | Power Terminals, M4 bolts       |
| Weight                             | W                 |       | 167   |      | g    |                                 |
| Case Isolation Voltage             | V <sub>isol</sub> | 4     |       |      | kV   | AC, 50 Hz, 1 minute             |
| Comparative Tracking Index         | СТІ               | 600   |       |      |      |                                 |
| Classica Distance                  |                   | 13.07 |       |      |      | Terminal to Terminal            |
| Clearance Distance                 |                   | 6.00  |       |      |      | Terminal to Heatsink            |
|                                    |                   | 14.27 |       |      | mm   | Terminal to Terminal            |
| Creepage Distance                  |                   | 12.34 |       |      |      | Terminal to Heatsink            |

### NTC Characteristics (T<sub>NTC</sub> = 25 °C unless otherwise specified)

| Parameter                       | Symbol             | Min. | Тур. | Max. | Unit | Notes |
|---------------------------------|--------------------|------|------|------|------|-------|
| Resistance at 25°C              | R <sub>25</sub>    |      | 4700 |      | Ω    |       |
| Tolerance of R <sub>25</sub>    |                    |      | ±1   |      | %    |       |
| Beta Value for 25°C to 85°C     | B <sub>25/85</sub> |      | 3435 |      | K    |       |
| Beta Value for 0°C to 100°C     | B <sub>0/100</sub> |      | 3399 |      | K    |       |
| Tolerance of B <sub>25/85</sub> |                    |      | ±1   |      | %    |       |
| Maximum Power Dissipation       | P <sub>Max</sub>   |      | 50   |      | mW   |       |

## Steinhart & Hart Coefficients for NTC Resistance & NTC Temperature Computation (T in K)

$$\ln\left(\frac{R}{R_{25}}\right) = A + \frac{B}{T} + \frac{C}{T^2} + \frac{D}{T^3}$$

$$\ln\left(\frac{R}{R_{25}}\right) = A + \frac{B}{T} + \frac{C}{T^2} + \frac{D}{T^3}$$

$$\frac{1}{T} = A_1 + B_1 \ln\left(\frac{R}{R_{25}}\right) + C_1 \ln^2\left(\frac{R}{R_{25}}\right) + D_1 \ln^3\left(\frac{R}{R_{25}}\right)$$

| $A_{1}$   | $B_1$     | $C_1$     | $D_1$     |
|-----------|-----------|-----------|-----------|
| 3.354E-03 | 3.001E-04 | 5.085E-06 | 2.188E-07 |

### **Typical Performance**

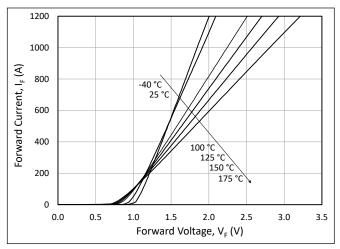


Figure 1. Typical Forward Characteristics

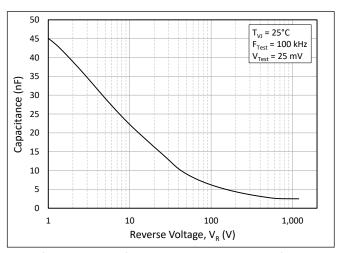
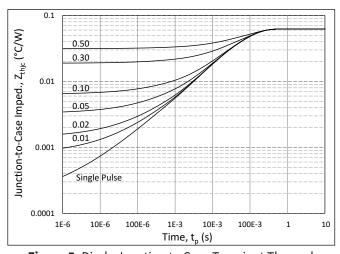


Figure 3. Typical Capacitance vs. Reverse Voltage



**Figure 5.** Diode Junction to Case Transient Thermal Impedance,  $Z_{th JC}$  (°C/W)

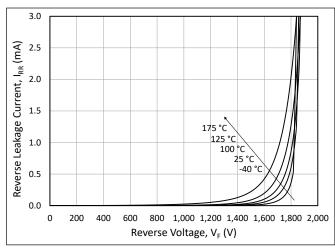


Figure 2. Typical Reverse Characteristics

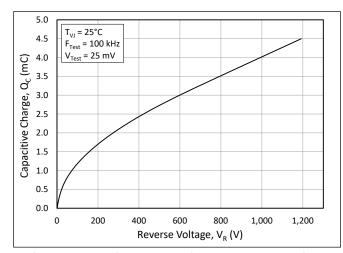


Figure 4. Typical Capacitive Charge vs. Reverse Voltage

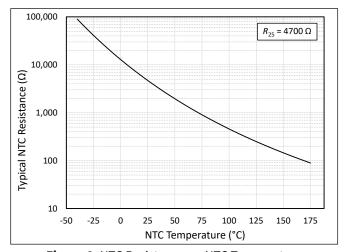
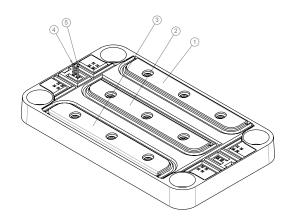


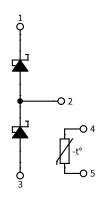
Figure 6. NTC Resistance vs. NTC Temperature

# 5

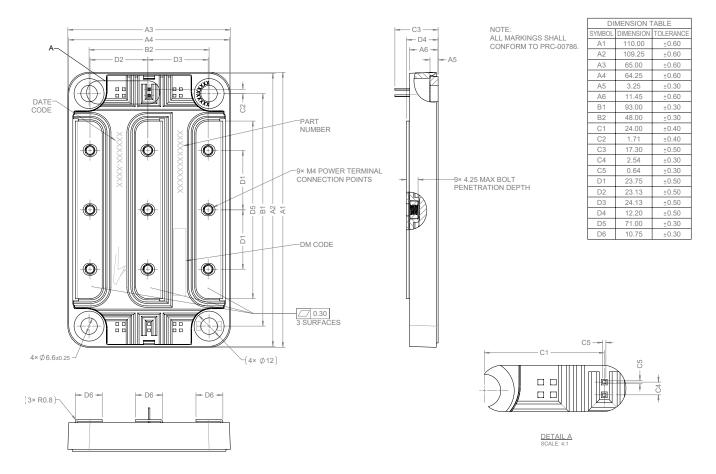
### **Schematic and Pin Out**



| PIN OUT SCHEME |       |  |  |  |  |
|----------------|-------|--|--|--|--|
| PIN            | LABEL |  |  |  |  |
| 1              | V+    |  |  |  |  |
| 2              | Mid   |  |  |  |  |
| 3              | V-    |  |  |  |  |
| 4              | NTC1  |  |  |  |  |
| (5)            | NTC2  |  |  |  |  |
|                |       |  |  |  |  |



### **Package Dimension (mm)**



### **Supporting Links & Tools**

### **Evaluation Tools & Support**

- CAR600M12HN6 PLECS Model
- SpeedFit 2.0 Design Simulator™
- Technical Support Forum

### **Application Notes**

- CPWR-AN35: 62mm Thermal Interface Material Application Note
- CPWR-AN39: KIT-CRD-CIL12N-HM User Guide

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